Switch-mode Power Rectifier 150 V, 30 A

Features and Benefits

- Low Forward Voltage
- Low Power Loss/High Efficiency
- High Surge Capability
- 30 A Total (15 A Per Diode Leg)
- Guard-Ring for Stress Protection
- These Devices are Pb-Free and are RoHS Compliant

Applications

- Power Supply Output Rectification
- Power Management
- Instrumentation

Mechanical Characteristics:

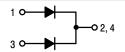
- Case: Epoxy, Molded
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight (Approximately): 1.9 Grams (TO-220 & TO-220FP)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds



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SCHOTTKY BARRIER RECTIFIER 30 AMPERES, 150 VOLTS



MARKING DIAGRAMS







TO-220 CASE 221A STYLE 6



A = Assembly Location

Y = Year
WW = Work Week
B30H150 = Device Code
G = Pb-Free Device
AKA = Polarity Designator

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

MAXIMUM RATINGS (Per Diode Leg)

Rating		Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		V _{RRM} V _{RWM} V _R	150	V
Average Rectified Forward Current (Rated V_R) $T_C = 124$ °C	(Per Leg) (Per Device)	I _{F(AV)}	15 30	А
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 6	60 Hz)	I _{FSM}	200	Α
Operating Junction Temperature (Note 1)		TJ	-20 to +150	°C
Storage Temperature		T _{stg}	-65 to +150	°C
Voltage Rate of Change (Rated V _R)		dv/dt	10,000	V/μs
ESD Ratings:	Machine Model = C Iuman Body Model = 3B		> 400 > 8000	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Rating		Symbol	Value	Unit
Maximum Thermal Resistance (MBR30H150CTG)	Junction-to-CaseJunction-to-Ambient	R _{θJC} R _{θJA}	2.0 45	°C/W
(MBRF30H150CTG)	- Junction-to-Case	R ₀ JC	2.5	

ELECTRICAL CHARACTERISTICS (Per Diode Leg)

Rating	Symbol	Тур	Max	Unit
Maximum Instantaneous Forward Voltage (Note 2) $ \begin{array}{l} (I_F=5~A,~T_C=25^\circ C)\\ (I_F=5~A,~T_C=125^\circ C)\\ (I_F=15~A,~T_C=25^\circ C)\\ (I_F=15~A,~T_C=125^\circ C) \end{array} $	VF	0.69 0.55 0.98 0.68	0.75 0.60 1.11 0.73	V
Maximum Instantaneous Reverse Current (Note 2) (Rated DC Voltage, T _C = 25°C) (Rated DC Voltage, T _C = 125°C)	İR		60 50	μA mA

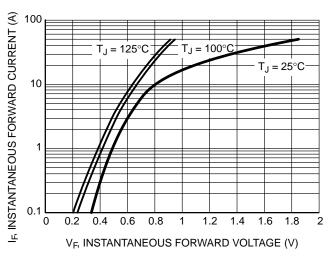
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 2. Pulse Test: Pulse Width = $300 \mu s$, Duty Cycle $\leq 2.0\%$.

DEVICE ORDERING INFORMATION

Device Order Number	Package Type	Shipping [†]
MBRF30H150CTG	TO-220FP (Pb-Free)	50 Units / Rail
MBR30H150CTG	TO-220 (Pb-Free)	50 Units / Rail

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

^{1.} The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.



T_J = 125°C T_J = 100°C T_J = 25°C T_J

Figure 1. Typical Forward Voltage

Figure 2. Maximum Forward Voltage

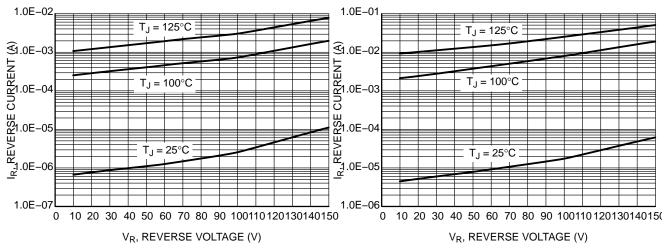


Figure 3. Typical Reverse Current

Figure 4. Maximum Reverse Current

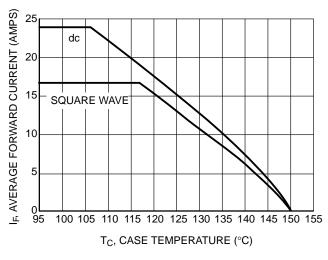


Figure 5. Current Derating

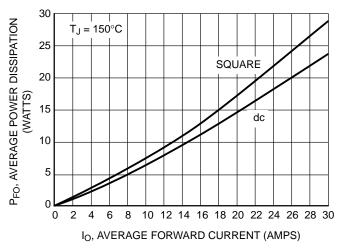


Figure 6. Forward Power Dissipation

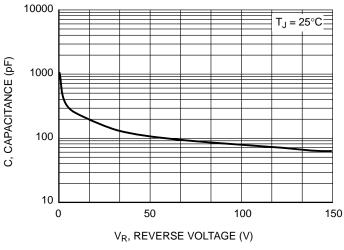


Figure 7. Capacitance

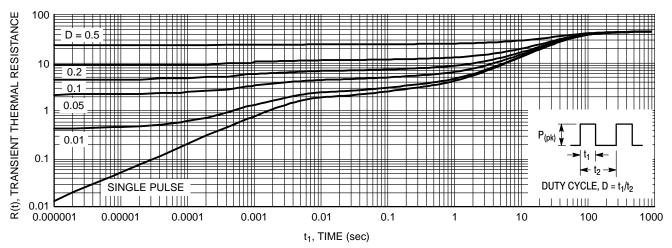


Figure 8. Thermal Response Junction-to-Ambient for MBR30H150CTG

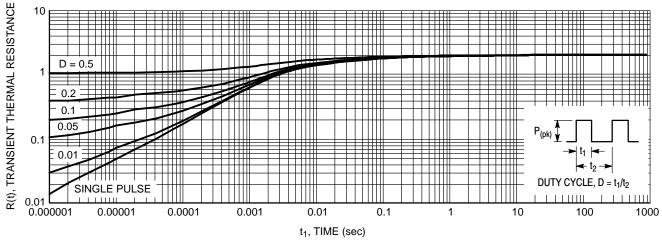


Figure 9. Thermal Response Junction-to-Case for MBR30H150CTG

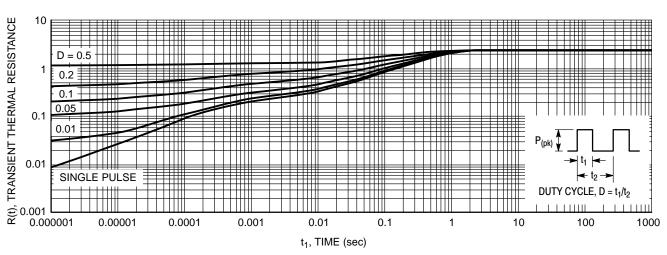
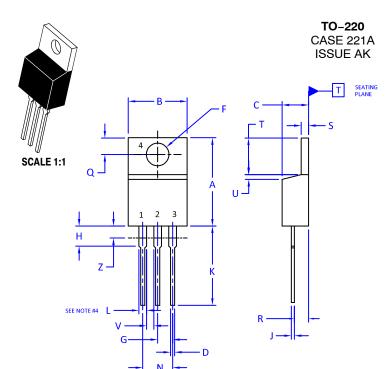


Figure 10. Thermal Response Junction-to-Case for MBRF30H150CTG

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DATE 13 JAN 2022

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: INCHES
- 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

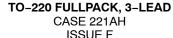
4. MAX WIDTH FOR F102 DEVICE = 1.35MM

	INCHES		MILLIMI	ETERS
DIM	MIN.	MAX.	MIN.	MAX.
Α	0.570	0.620	14.48	15.75
В	0.380	0.415	9.66	10.53
С	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.60	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.41
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045		1.15	
Z		0.080		2.04

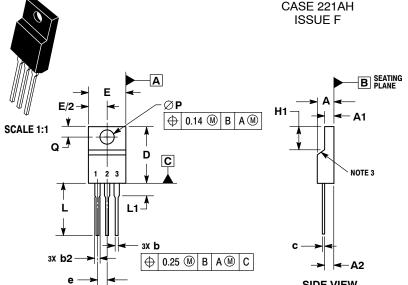
STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:	
PIN 1.	BASE	PIN 1.	BASE	PIN 1.	CATHODE	PIN 1.	MAIN TERMINAL 1
2.	COLLECTOR	2.	EMITTER	2.	ANODE	2.	MAIN TERMINAL 2
3.	EMITTER	3.	COLLECTOR	3.	GATE	3.	GATE
4.	COLLECTOR	4.	EMITTER	4.	ANODE	4.	MAIN TERMINAL 2
STYLE 5:		STYLE 6:		STYLE 7:		STYLE 8:	
PIN 1.	GATE	PIN 1.	ANODE	PIN 1.	CATHODE	PIN 1.	CATHODE
2.	DRAIN	2.	CATHODE	2.	ANODE	2.	ANODE
3.	SOURCE	3.	ANODE	3.	CATHODE	3.	EXTERNAL TRIP/DELAY
4.	DRAIN	4.	CATHODE	4.	ANODE	4.	ANODE
STYLE 9:		STYLE 10:		STYLE 11:		STYLE 12:	
PIN 1.	GATE	PIN 1.	GATE	PIN 1.	DRAIN	PIN 1.	MAIN TERMINAL 1
2.	COLLECTOR	2.	SOURCE	2.	SOURCE	2.	MAIN TERMINAL 2
3.	EMITTER	3.	DRAIN	3.	GATE	3.	GATE
4.	COLLECTOR	4.	SOURCE	4.	SOURCE	4.	NOT CONNECTED

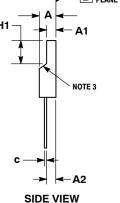
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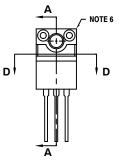
DATE 30 SEP 2014

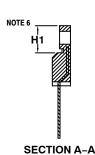






FRONT VIEW





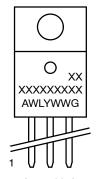
ALTERNATE CONSTRUCTION

NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. CONTOUR UNCONTROLLED IN THIS AREA.
- CONTOUR ONCOUNTIOLLED IN THIS AREA.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH AND GATE PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE TO BE MEASURED AT OUTERMOST EXTREME OF THE PLASTIC BODY.
 DIMENSION b2 DOES NOT INCLUDE DAMBAR PROTRUSION.
 LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 2.00.
- CONTOURS AND FEATURES OF THE MOLDED PACKAGE BODY MAY VARY WITHIN THE ENVELOP DEFINED BY DIMENSIONS AT AND H1 FOR MANUFACTURING PURPOSES.

	MILLIMETERS			
DIM	MIN	MAX		
Α	4.30	4.70		
A1	2.50	2.90		
A2	2.50	2.90		
b	0.54	0.84		
b2	1.10	1.40		
С	0.49	0.79		
D	14.70	15.30		
E	9.70	10.30		
е	2.54	BSC		
H1	6.60	7.10		
L	12.50	14.73		
L1		2.80		
P	3.00	3.40		
Q	2.80	3.20		

GENERIC MARKING DIAGRAM*



= Assembly Location

WL = Wafer Lot

= Year

WW = Work Week

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1:		STYLE 2:	
PIN 1.	MAIN TERMINAL 1	PIN 1.	CATHODE
2.	MAIN TERMINAL 2	2.	ANODE
3.	GATE	3.	GATE

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DESCRIPTION:	TO-220 FULLPACK. 3-LEA	AD	PAGE 1 OF 1

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